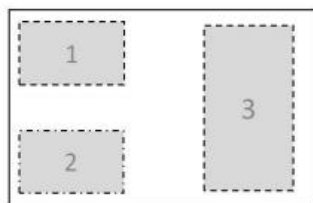
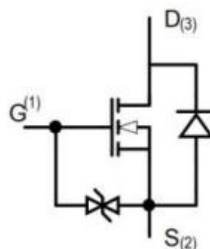


**DFN1006-3L 20V N Channel Enhancement ESD Protection 沟道增强型带静电保护
MOS Field Effect Transistor 场效应管**



top view



■ **Absolute Maximum Ratings 最大额定值**

Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Drain-Source Voltage 漏极-源极电压	BV_{DSS}	20	V
Gate- Source Voltage 栅极-源极电压	V_{GS}	± 10	V
Drain Current (continuous)漏极电流-连续	I_D (at $T_A = 25^\circ C$)	0.7	A
Drain Current (pulsed)漏极电流-脉冲	I_{DM}	1.8	A
Total Device Dissipation 总耗散功率	P_D (at $T_A = 25^\circ C$)	150	mW
Thermal Resistance Junction-Ambient 热阻	$R_{\theta JA}$	1250	$^\circ C/W$
ESD Protected Up to 人体模式静电保护范围	ESD(HBM)	1.2	kV
Junction/Storage Temperature 结温/储存温度	T_J, T_{stg}	125 $^\circ C$, -50~150 $^\circ C$	

■ **Device Marking 产品字标**

FS3134KD=34

Electrical Characteristics 电特性

 (T_A=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位
Drain-Source Breakdown Voltage 漏极-源极击穿电压(I _D =250uA, V _{GS} =0V)	BV _{DSS}	20	—	—	V
Gate Threshold Voltage 栅极开启电压(I _D =250uA, V _{GS} =V _{DS})	V _{GS(th)}	0.45	0.7	1.1	V
Zero Gate Voltage Drain Current 零栅压漏极电流(V _{GS} =0V, V _{DS} =20V)	I _{DSS}	—	—	1	μA
Gate Body Leakage 栅极漏电流(V _{GS} =±10V, V _{DS} =0V)	I _{GSS}	—	—	±10	μA
Static Drain-Source On-State Resistance 静态漏源导通电阻(I _D =0.5A, V _{GS} =4.5V) (I _D =0.5A, V _{GS} =2.5V)	R _{DS(ON)}	—	220 280	350 420	mΩ
Diode Forward Voltage Drop 内附二极管正向压降(I _{SD} =0.8A, V _{GS} =0V)	V _{SD}	—	—	1.2	V
Input Capacitance 输入电容 (V _{GS} =0V, V _{DS} =10V, f=1MHz)	C _{ISS}	—	43.6	—	pF
Common Source Output Capacitance 共源输出电容(V _{GS} =0V, V _{DS} =10V, f=1MHz)	C _{OSS}	—	6.8	—	pF
Reverse Transfer Capacitance 反馈电容(V _{GS} =0V, V _{DS} =10V, f=1MHz)	C _{RSS}	—	4.6	—	pF
Total Gate Charge 栅极电荷密度 (V _{DS} =10V, I _D =0.5A, V _{GS} =4.5V)	Q _g	—	0.8	—	nC
Gate Source Charge 栅源电荷密度 (V _{DS} =10V, I _D =0.5A, V _{GS} =4.5V)	Q _{gs}	—	0.3	—	nC
Gate Drain Charge 栅漏电荷密度 (V _{DS} =10V, I _D =0.5A, V _{GS} =4.5V)	Q _{gd}	—	0.15	—	nC
Turn-ON Delay Time 开启延迟时间 (V _{DS} =10V I _D =0.5A, R _{GEN} =10Ω, V _{GS} =4.5V)	t _{d(on)}	—	1.4	—	ns
Turn-ON Rise Time 开启上升时间 (V _{DS} =10V I _D =0.5A, R _{GEN} =10Ω, V _{GS} =4.5V)	t _r	—	27.8	—	ns
Turn-OFF Delay Time 关断延迟时间 (V _{DS} =10V I _D =0.5A, R _{GEN} =10Ω, V _{GS} =4.5V)	t _{d(off)}	—	54.6	—	ns
Turn-OFF Fall Time 关断下降时间 (V _{DS} =10V I _D =0.5A, R _{GEN} =10Ω, V _{GS} =4.5V)	t _f	—	25.6	—	ns

■ Typical Characteristic Curve 典型特性曲线

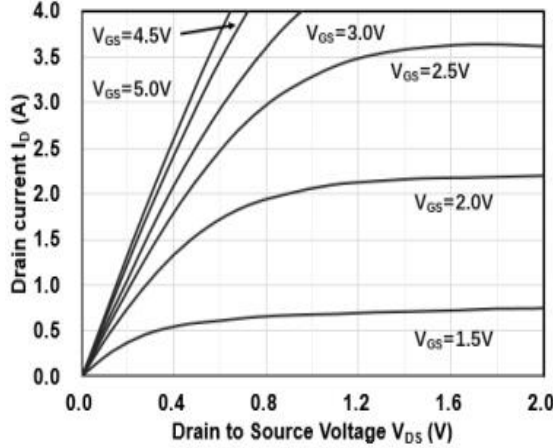


Figure 1: Output Characteristics

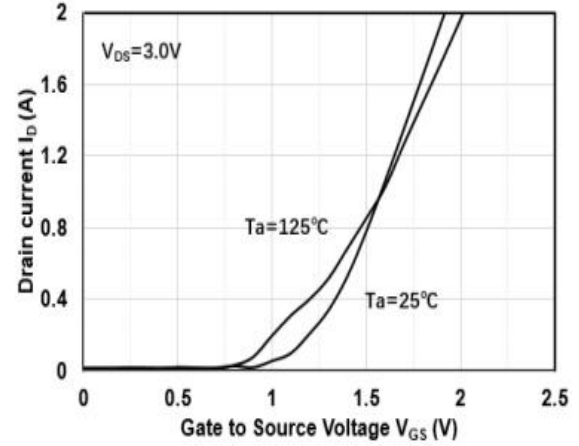


Figure 2: Transfer Characteristics

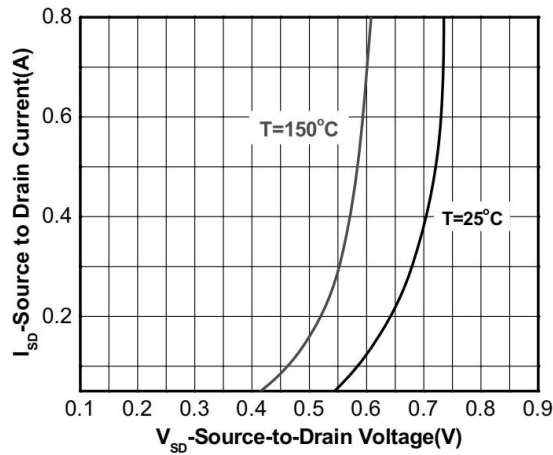


Figure 3: Diode Characteristics

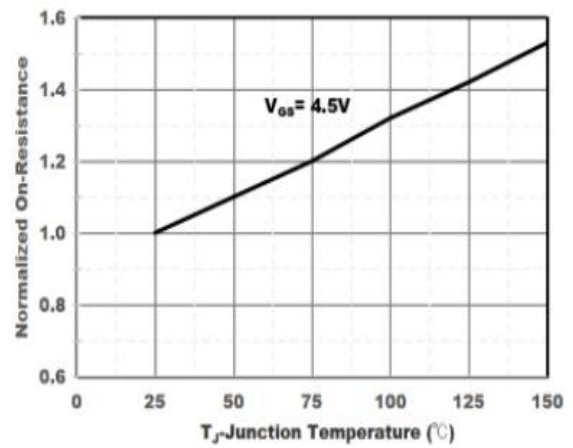


Figure 4: On-Resistance vs. Temperature

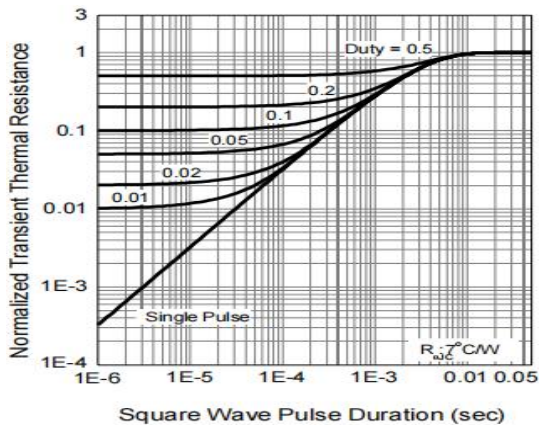


Figure 5: Transient Thermal Response Curve

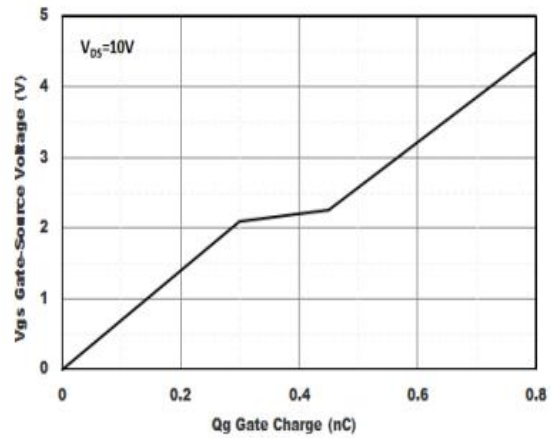
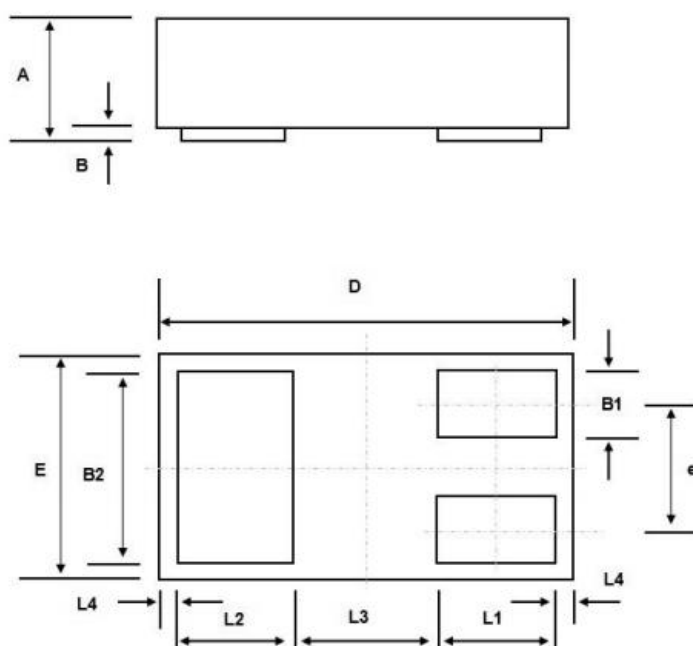


Figure 6: Gate-Charge Characteristics

■ **Dimension 外形封装尺寸**

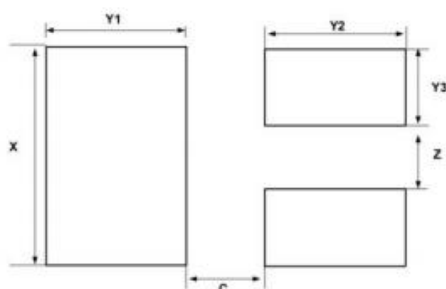
Package Outline Dimensions

DFN1006-3L



Symbol	Dimensions In Millimet	
	Min	Max
A	0.33	0.50
B	0.00	0.05
B1	0.10	0.20
B2	0.45	0.55
D	0.90	1.05
E	0.50	0.65
e	0.35	
L1	0.20	0.30
L2	0.20	0.30
L3	0.39	
L4	0.05	

Suggested Pad Layout (mm)



Symbol	Dimensions
C	0.25
X	0.65
Y1	0.50
Y2	0.50
Y3	0.25
Z	0.20